



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

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Serial No.: Unknown

Filed: May 3, 2001

For: METHOD OF FORMING A SUBSTRATE
CONTACT IN A FIELD EFFECT
TRANSISTOR FORMED OVER A
BURIED INSULATOR LAYER

Group Art Unit: Unknown

Examiner: Unknown

Att'y Docket: 2000.064400/DE0058

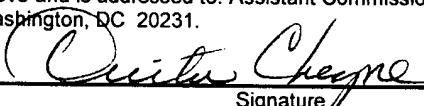
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Assistant Commissioner for Patents
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Sir:

Transmitted for filing herewith is the certified copy of the priority document – German
Patent Application No. 100 54 109.7 filed on October 31, 2000.

If any fees under 37 C.F.R. §§ 1.16 to 1.21 be required for any reason relating to the
enclosed materials, the Assistant Commissioner is authorized to said fees Advanced Micro
Devices, Inc. Deposit Account No. 01-0365/DE0058.

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Respectfully submitted,



Date: May 3, 2001

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Prioritätsbescheinigung über die Einreichung einer Patentanmeldung

Aktenzeichen: 100 54 109.7

Anmeldetag: 31. Oktober 2000

Anmelder/Inhaber: ADVANCED MICRO DEVICES, INC., Sunnyvale, Calif./US

Bezeichnung: A METHOD OF FORMING A SUBSTRATE CONTACT IN A FIELD EFFECT TRANSISTOR FORMED OVER A BURIED INSULATOR LAYER

IPC: H 01 L 21/336

Die angehefteten Stücke sind eine richtige und genaue Wiedergabe der ursprünglichen Unterlagen dieser Patentanmeldung.

München, den 1. März 2001
Deutsches Patent- und Markenamt
Der Präsident
Im Auftrag